

Taiwan Semiconductor

## 30A, 45V - 150V Schottky Barrier Rectifier

### **FEATURES**

- Low power loss, high efficiency
- Guard ring for overvoltage protection
- High surge current capability
- RoHS Compliant
- Halogen-free according to IEC 61249-2-21

## APPLICATIONS

- Switching mode power supply (SMPS)
- Adapters
- DC to DC converters

## **MECHANICAL DATA**

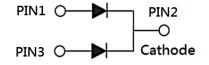
- Case: TO-220AB
- Molding compound meets UL 94V-0 flammability rating
- Terminal: Matte tin plated leads, solderable per J-STD-002
- Mounting torque: 0.56 N·m maximum
- Meet JESD 201 class 1A whisker test
- Polarity: As marked
- Weight: 1.90g (approximately)

KEY PARAMETERS		
PARAMETER	VALUE	UNIT
I <sub>F</sub>	30	А
V <sub>RRM</sub>	45 - 150	V
I <sub>FSM</sub>	200	А
T <sub>J MAX</sub>	150	°C
Package	TO-220AB	
Configuration	Dual d	lies









		MBR	MBR	MBR	MBR	MBR	
PARAMETER	SYMBOL	3045	3060	3080	30100	30150	UNIT
		CT-Y	CT-Y	CT-Y	CT-Y	CT-Y	
Marking code on the device		MBR 3045CT	MBR 3060CT	MBR 3080CT	MBR 30100CT	MBR 30150CT	
Repetitive peak reverse voltage	$V_{RRM}$	45	60	80	100	150	V
Reverse voltage, total rms value	V <sub>R(RMS)</sub>	31	42	56	70	105	V
Forward current	١ <sub>F</sub>	30		А			
Surge peak forward current, 8.3ms single half sine wave superimposed on rated load	I <sub>FSM</sub>	200		A			
Peak repetitive reverse surge current <sup>(1)</sup>	I <sub>RRM</sub>	1 0.5			A		
Peak repetitive forward current (Rated $V_R$ , Square wave, 20KHz)	I <sub>FRM</sub>	30		А			
Critical rate of rise of off-state voltage	dv/dt	10,000			V/µs		
Junction temperature	TJ	-55 to +150			°C		
Storage temperature	T <sub>STG</sub>	-55 to +150			°C		

#### Notes:

1. tp = 2.0µs, 1.0KHz



THERMAL PERFORMANCE				
PARAMETER		SYMBOL	ТҮР	UNIT
Junction-to-case thermal resistance	MBR3045CT-Y MBR3060CT-Y MBR3080CT-Y	R <sub>ejc</sub>	1.0	°C/W
Junction-to-case thermal resistance	MBR30100CT-Y MBR30150CT-Y	R <sub>eJC</sub>	1.5	°C/W

PARAMETER		CONDITIONS	SYMBOL	ТҮР	MAX	UNIT
	MBR3045CT-Y	I <sub>F</sub> = 15A, T <sub>J</sub> = 25°C		-	0.70	V
	MBR3060CT-Y			-	0.77	V
	MBR3080CT-Y MBR30100CT-Y			-	0.84	V
	MBR30150CT-Y			-	0.95	V
	MBR3045CT-Y			-	0.82	V
	MBR3060CT-Y			-	-	V
	MBR3080CT-Y MBR30100CT-Y	I <sub>F</sub> = 30A, T <sub>J</sub> = 25°C		-	0.94	V
Forward voltage per	MBR30150CT-Y			-	1.02	V
diode <sup>(1)</sup>	MBR3045CT-Y	I <sub>F</sub> = 15A, T <sub>J</sub> = 125°C	V <sub>F</sub>	-	0.60	V
	MBR3060CT-Y			-	0.67	V
	MBR3080CT-Y MBR30100CT-Y			-	0.70	V
	MBR30150CT-Y			-	0.92	V
	MBR3045CT-Y	I <sub>F</sub> = 30A, T <sub>J</sub> = 125°C		-	0.73	V
	MBR3060CT-Y			-	-	V
	MBR3080CT-Y MBR30100CT-Y			-	0.82	V
	MBR30150CT-Y			-	0.98	V
Reverse current @ rated $V_R$ per diode <sup>(2)</sup>	MBR3045CT-Y MBR3060CT-Y MBR3080CT-Y MBR30100CT-Y	T <sub>J</sub> = 25°C		-	200	μA
	MBR30150CT-Y			-	100	μA
	MBR3045CT-Y	T <sub>J</sub> = 125°C	I <sub>R</sub>	-	40	mA
	MBR3060CT-Y			-	10	mA
	MBR3080CT-Y MBR30100CT-Y			-	7.5	mA
	MBR30150CT-Y			-	5	mA

#### Notes:

1. Pulse test with PW = 0.3ms

2. Pulse test with PW = 30ms

ORDERING INFORMATION		
ORDERING CODE <sup>(1)</sup>	PACKAGE	PACKING
MBR30xCT-Y	TO-220AB	50 / Tube

Notes:

1. "x" defines voltage from 45V(MBR3045CT-Y) to 150V(MBR30150CT-Y)



**INSTANTANEOUS REVERSE CURRENT (mA)** 

100

10

1

0.1

0.01

0.001

20 30 40 50

10

MBR3045CT-Y

MBR3060CT-Y-30150CT-Y

## MBR3045CT-Y - MBR30150CT-Y

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## **CHARACTERISTICS CURVES**

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ 

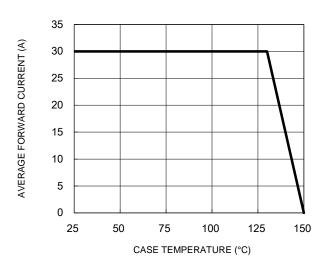


Fig.1 Forward Current Derating Curve

#### **Fig.3 Typical Reverse Characteristics**

T\_=125°C

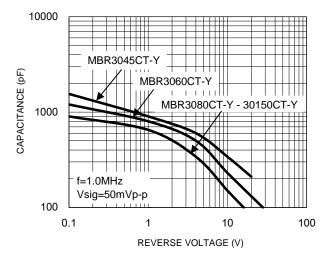
T<sub>1</sub>=75°C

T\_=25°C

60 70

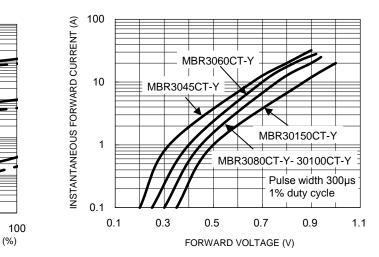
PERCENT OF RATED PEAK REVERSE VOLTAGE (%)

80 90



#### **Fig.2 Typical Junction Capacitance**

**Fig.4 Typical Forward Characteristics** 

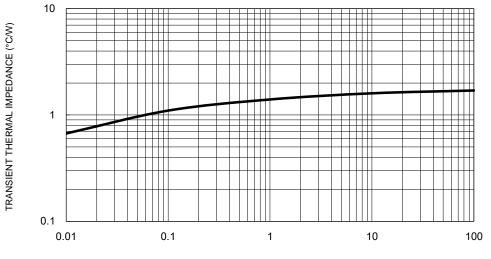


### Fig.5 Maximum Non-Repetitive Forward Surge Current 225 200 PEAK FORWARD SURGE CURRENT (A) 8.3ms single half sine wave 175 150 125 100 75 50 25 0 1 10 100 NUMBER OF CYCLES AT 60 Hz



## **CHARACTERISTICS CURVES**

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ 

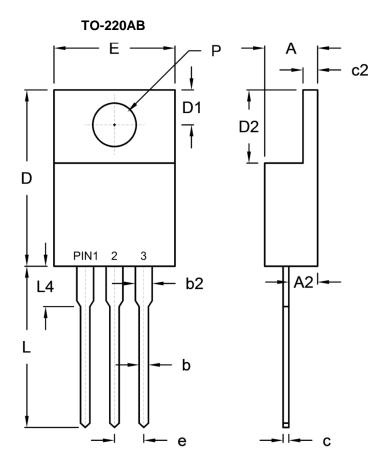


### Fig.6 Typical Transient Thermal Impedance

PULSE DURATION (s)

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## PACKAGE OUTLINE DIMENSIONS



DIM.	Unit (mm)		Unit (	(inch)	
	Min.	Max.	Min.	Max.	
A	4.42	4.76	0.174	0.187	
A2	2.20	2.80	0.087	0.110	
b	0.68	0.94	0.027	0.037	
b2	1.14	1.77	0.045	0.070	
с	0.35	0.64	0.014	0.025	
c2	1.14	1.40	0.045	0.055	
D	14.60	16.00	0.575	0.630	
D1	2.62	3.44	0.103	0.135	
D2	5.84	6.86	0.230	0.270	
E	-	10.50	-	0.413	
е	2.41	2.67	0.095	0.105	
L	13.19	14.79	0.519	0.582	
L4	2.80	4.20	0.110	0.165	
Р	3.54	4.00	0.139	0.157	

## **MARKING DIAGRAM**



P/N	= Marking Code
G	= Green Compound
YWW	= Date Code
F	= Factory Code



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